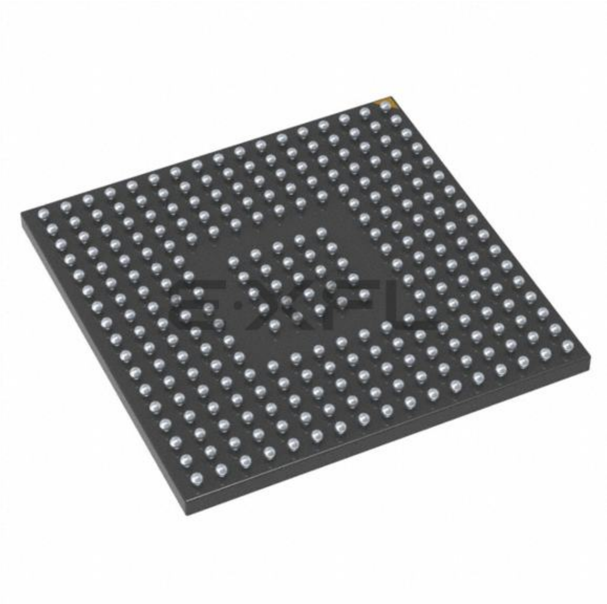

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	140
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	201-UFBGA
Supplier Device Package	176+25UFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f427igh7

Table 2. STM32F427xx and STM32F429xx features and peripheral counts (continued)

Peripherals		STM32F427 Vx	STM32F429Vx	STM32F427 Zx	STM32F429Zx	STM32F427 Ax	STM32F429 Ax	STM32F427 Ix	STM32F429Ix	STM32F429Bx	STM32F429Nx
Communication interfaces	SPI / I^2S	4/2 (full duplex)(2)		6/2 (full duplex)(2)							
	I^2C	3									
	USART/ UART	4/4									
	USB OTG FS	Yes									
	USB OTG HS	Yes									
	CAN	2									
	SAI	1									
	SDIO	Yes									
Camera interface		Yes									
LCD-TFT (STM32F429xx only)		No	Yes	No	Yes	No	Yes	No	Yes		
Chrom-ART Accelerator™		Yes									
GPIOs		82		114		130		140		168	
12-bit ADC Number of channels		3									
		16		24							
12-bit DAC Number of channels		Yes 2									
Maximum CPU frequency		180 MHz									
Operating voltage		1.8 to 3.6 V(3)									
Operating temperatures		Ambient temperatures: –40 to +85 °C /–40 to +105 °C									
		Junction temperature: –40 to + 125 °C									
Packages		LQFP100		WLCSP143 LQFP144		UFBGA169		UFBGA176 LQFP176		LQFP208	TFBGA216

1. For the LQFP100 package, only FMC Bank1 or Bank2 are available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select. Bank2 can only support a 16- or 8-bit NAND Flash memory using the NCE2 Chip Select. The interrupt line cannot be used since Port G is not available in this package. For UFBGA169 package, only SDRAM, NAND and multiplexed static memories are supported.
2. The SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I2S audio mode.
3. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to *Section 3.17.2: Internal reset OFF*).

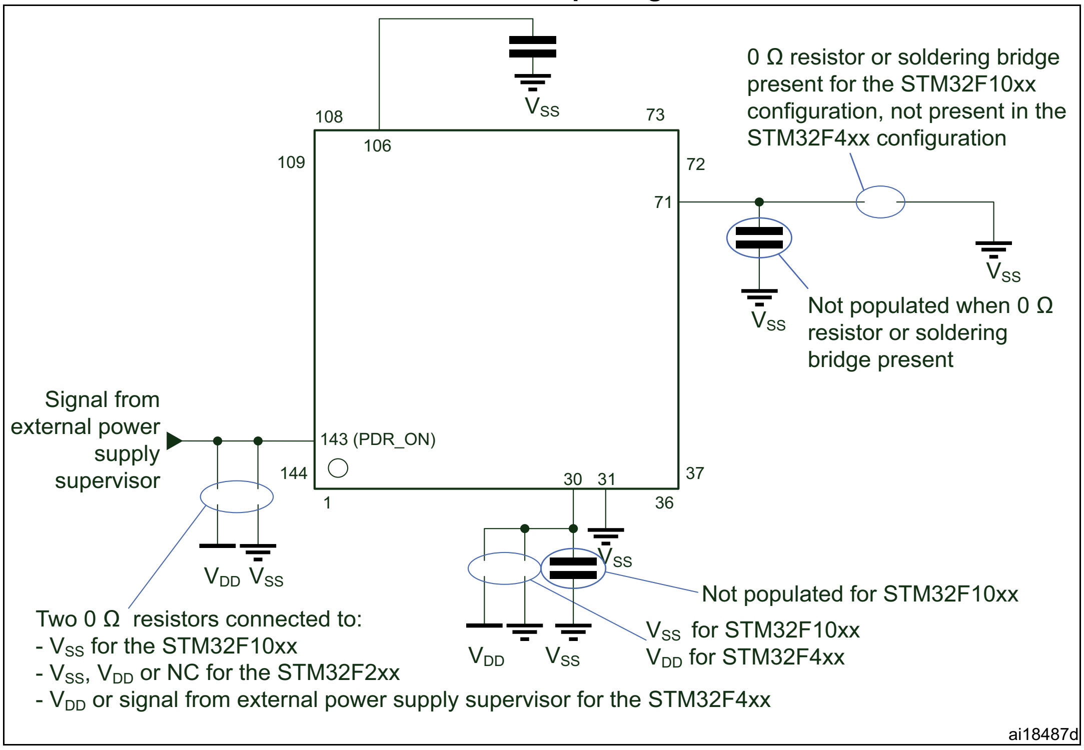


Figure 2. Compatible board design between STM32F10xx/STM32F2xx/STM32F4xx for LQFP144 package

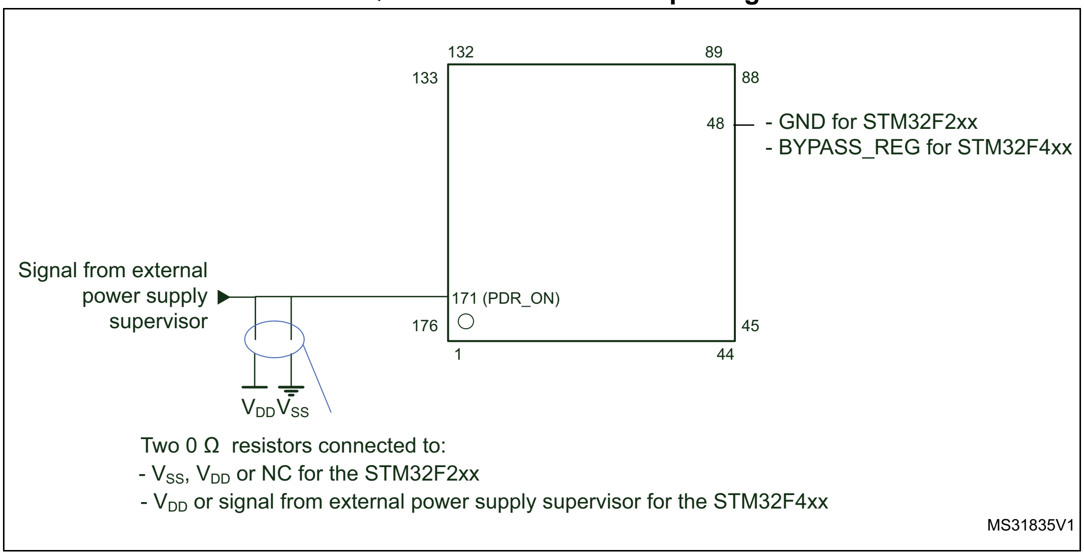


Figure 3. Compatible board design between STM32F2xx and STM32F4xx for LQFP176 and UFBGA176 packages

Additional 32-bit registers contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the V_{BAT} pin.

3.20 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

  The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled.

  The voltage regulator can be put either in main regulator mode (MR) or in low-power mode (LPR). Both modes can be configured as follows (see *Table 5: Voltage regulator modes in stop mode*):

  – Normal mode (default mode when MR or LPR is enabled)

  – Under-drive mode.

  The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup).

Table 5. Voltage regulator modes in stop mode

Voltage regulator configuration	Main regulator (MR)	Low-power regulator (LPR)
Normal mode	MR ON	LPR ON
Under-drive mode	MR in under-drive mode	LPR in under-drive mode

- **Standby mode**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

  The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

  The standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

Table 15. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all V_{DD_x} power lines (source)(1)	270	mA
ΣI_{VSS}	Total current out of sum of all V_{SS_x} ground lines (sink)(1)	− 270	
I_{VDD}	Maximum current into each V_{DD_x} power line (source)(1)	100	
I_{VSS}	Maximum current out of each V_{SS_x} ground line (sink)(1)	− 100	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/Os and control pin	− 25	
ΣI_{IO}	Total output current sunk by sum of all I/O and control pins (2)	120	
	Total output current sourced by sum of all I/Os and control pins(2)	− 120	
$I_{INJ(PIN)}$ (3)	Injected current on FT pins (4)	− 5/+0	
	Injected current on NRST and BOOT0 pins (4)		
	Injected current on TTa pins(5)	±5	
$\Sigma I_{INJ(PIN)}$(5)	Total injected current (sum of all I/O and control pins)(6)	±25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Negative injection disturbs the analog performance of the device. See note in *Section 6.3.21: 12-bit ADC characteristics*.
4. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
5. A positive injection is induced by $V_{IN}>V_{DDA}$ while a negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 14* for the values of the maximum allowed input voltage.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 16. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	− 65 to +150	°C
T_J	Maximum junction temperature	125	°C

Table 28. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions	Typ(1)			Max(2)			Unit
			T_A = 25 °C			T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
			V_{DD} = 1.7 V	V_{DD}= 2.4 V	V_{DD} = 3.3 V	V_{DD} = 3.6 V			
I_{DD_STBY}	Supply current in Standby mode	Backup SRAM ON, low-speed oscillator (LSE) and RTC ON	2.80	3.00	3.60	7.00	19.00	36.00	µA
		Backup SRAM OFF, low-speed oscillator (LSE) and RTC ON	2.30	2.60	3.10	6.00	16.00	31.00	
		Backup SRAM ON, RTC and LSE OFF	2.30	2.50	2.90	6.00(3)	18.00(3)	35.00(3)	
		Backup SRAM OFF, RTC and LSE OFF	1.70	1.90	2.20	5.00(3)	15.00(3)	30.00(3)	

1. The typical current consumption values are given with PDR OFF (internal reset OFF). When the PDR is OFF (internal reset OFF), the typical current consumption is reduced by additional 1.2 µA.
2. Based on characterization, not tested in production unless otherwise specified.
3. Based on characterization, tested in production.

Table 29. Typical and maximum current consumptions in V_{BAT} mode

Symbol	Parameter	Conditions(1)	Typ			Max(2)		Unit
			T_A = 25 °C			T_A = 85 °C	T_A = 105 °C	
			V_{BAT} = 1.7 V	V_{BAT}= 2.4 V	V_{BAT} = 3.3 V	V_{BAT} = 3.6 V		
I_{DD_VBAT}	Backup domain supply current	Backup SRAM ON, low-speed oscillator (LSE) and RTC ON	1.28	1.40	1.62	6	11	µA
		Backup SRAM OFF, low-speed oscillator (LSE) and RTC ON	0.66	0.76	0.97	3	5	
		Backup SRAM ON, RTC and LSE OFF	0.70	0.72	0.74	5	10	
		Backup SRAM OFF, RTC and LSE OFF	0.10	0.10	0.10	2	4	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a C_L of 6 pF for typical values.
2. Guaranteed by characterization results.

Figure 33 and *Figure 34* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 33. PLL output clock waveforms in center spread mode

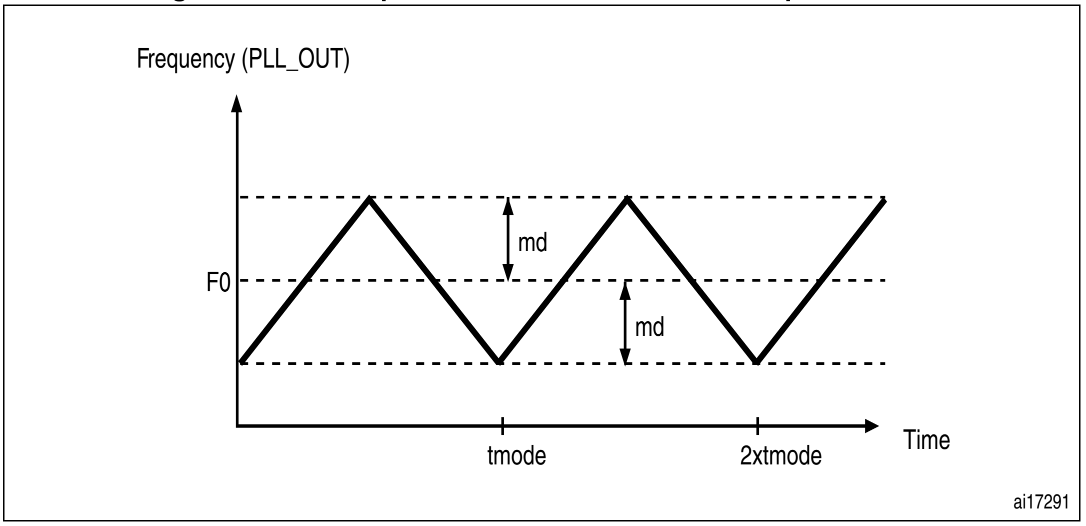
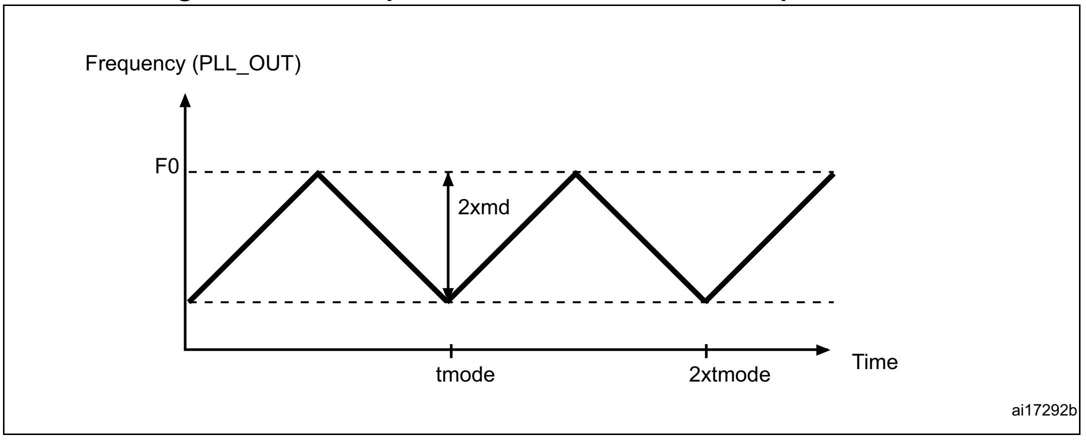


Figure 34. PLL output clock waveforms in down spread mode



6.3.16 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in *Table 55*.

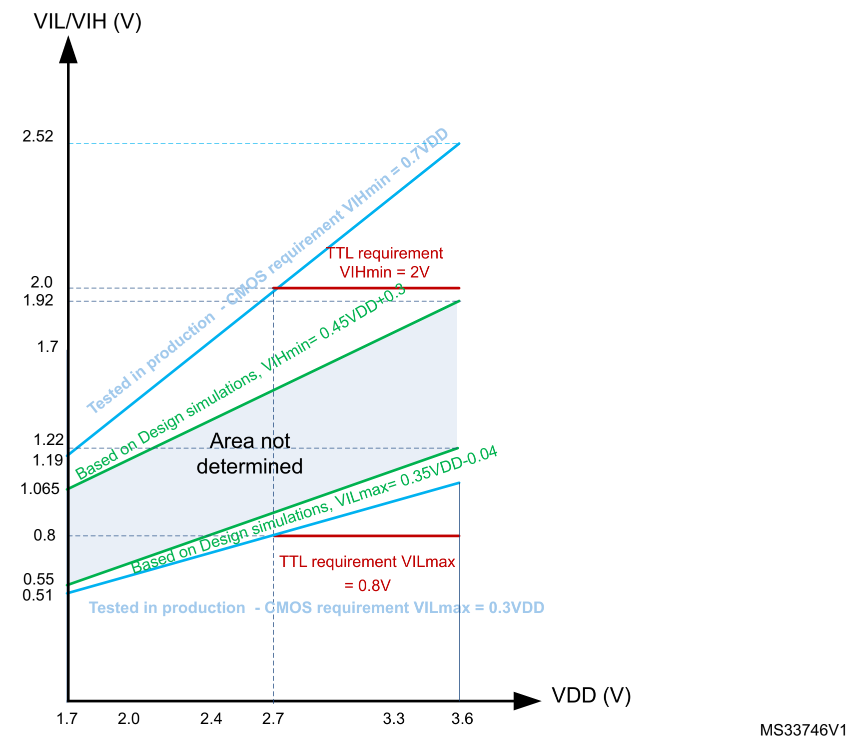
Table 55. I/O current injection susceptibility(1)

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0 pin	− 0	NA	mA
	Injected current on NRST pin	− 0	NA	
	Injected current on PA0, PA1, PA2, PA3, PA6, PA7, PB0, PC0, PC1, PC2, PC3, PC4, PC5, PH1, PH2, PH3, PH4, PH5	− 0	NA	
	Injected current on TTa pins: PA4 and PA5	− 0	+5	
	Injected current on any other FT pin	− 5	NA	

1. NA = not applicable.

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Figure 35. FT I/O input characteristics



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14, PC15 and PI8 which can sink or source up to ±3mA. When using the PC13 to PC15 and PI8 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*. In particular:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 15*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 15*).

6.3.18 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 56: I/O static characteristics*).

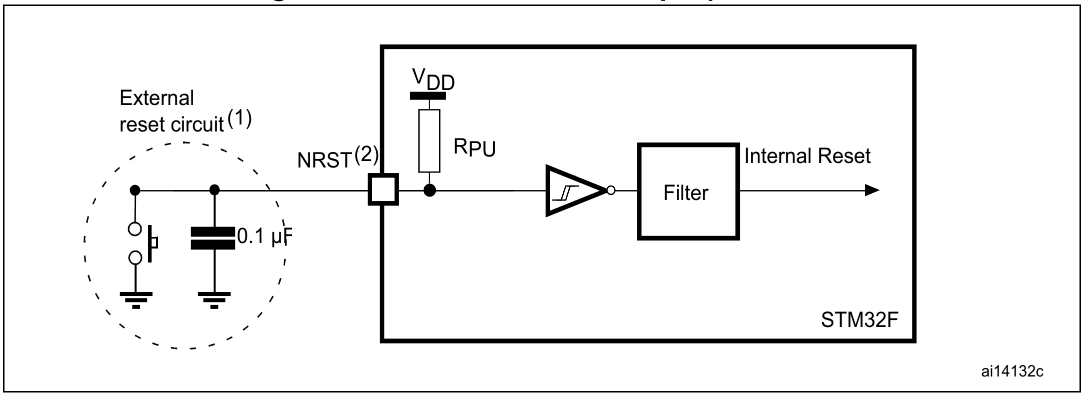
Unless otherwise specified, the parameters given in *Table 59* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

Table 59. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor(1)	$V_{IN} = V_{SS}$	30	40	50	kΩ
$V_{F(NRST)}$(2)	NRST Input filtered pulse		-	-	100	ns
$V_{NF(NRST)}$(2)	NRST Input not filtered pulse	V_{DD} > 2.7 V	300	-	-	ns
T_{NRST_OUT}	Generated reset pulse duration	Internal Reset source	20	-	-	µs

1. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).
2. Guaranteed by design.

Figure 37. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The external capacitor must be placed as close as possible to the device.
3. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 59*. Otherwise the reset is not taken into account by the device.

Figure 38. SPI timing diagram - slave mode and CPHA = 0

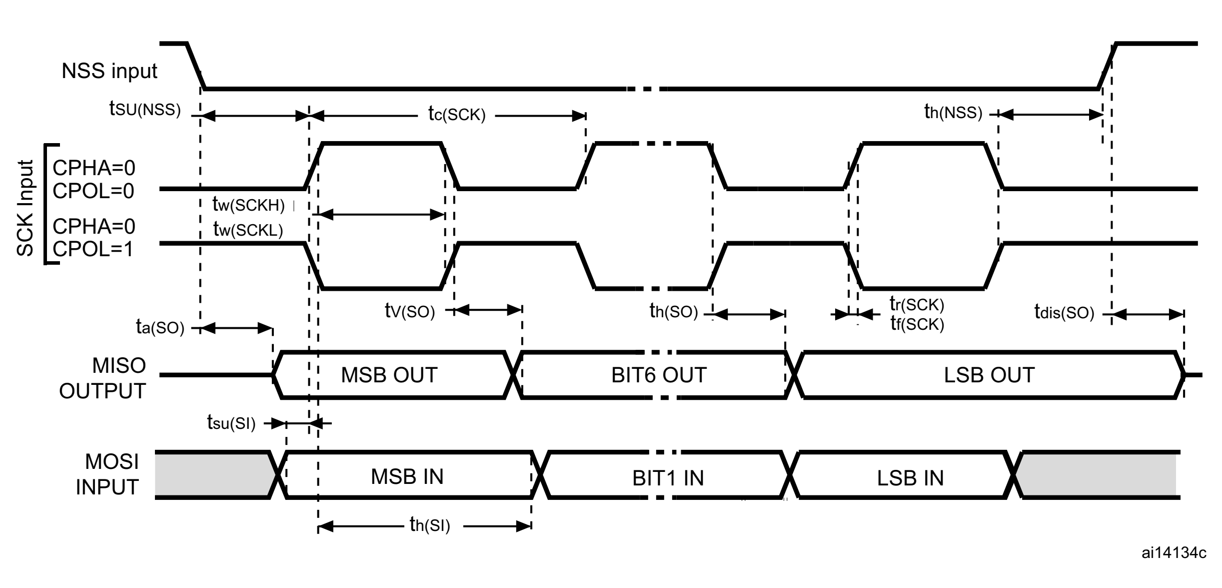
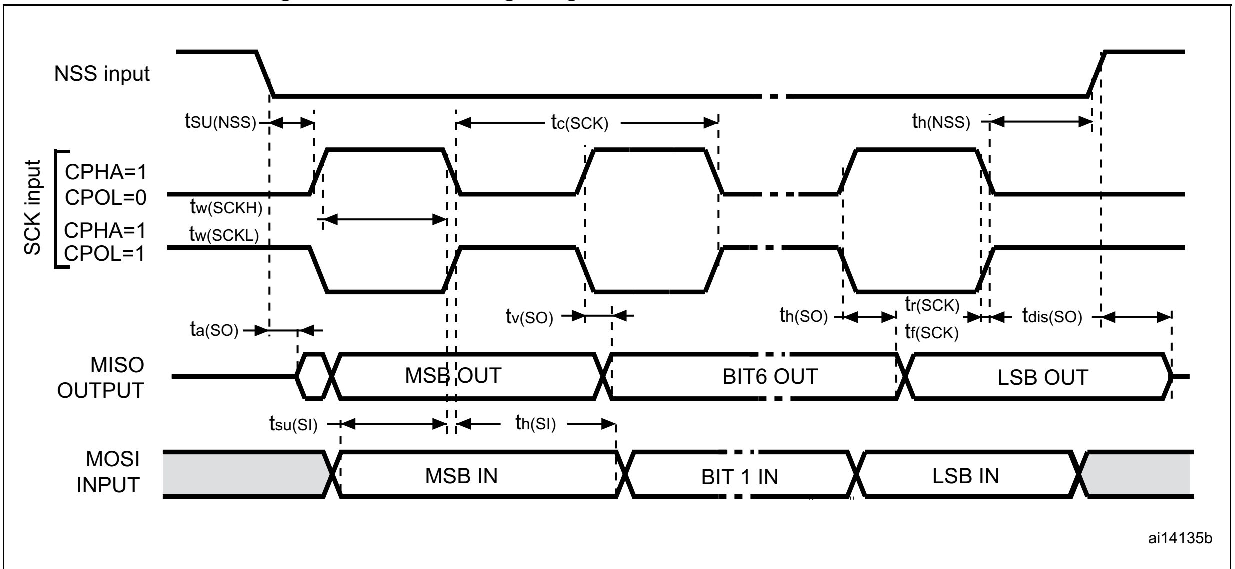


Figure 39. SPI timing diagram - slave mode and CPHA = 1



SAI characteristics

Unless otherwise specified, the parameters given in *Table 64* for SAI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and VDD supply voltage conditions summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C=30 pF
- Measurement points are performed at CMOS levels: $0.5V_{DD}$

Refer to *Section 6.3.17: I/O port characteristics* for more details on the input/output alternate function characteristics (SCK,SD,WS).

Table 64. SAI characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCKL}	SAI Main clock output	-	256 x 8K	256xFs(2)	MHz
F_{SCK}	SAI clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D_{SCK}	SAI clock frequency duty cycle	Slave receiver	30	70	%
$t_{v(FS)}$	FS valid time	Master mode	8	22	ns
$t_{su(FS)}$	FS setup time	Slave mode	2	-	
$t_{h(FS)}$	FS hold time	Master mode	8	-	
		Slave mode	0	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	5	-	
$t_{su(SD\_SR)}$		Slave receiver	3	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	0	-	
$t_{h(SD\_SR)}$		Slave receiver	0	-	
$t_{v(SD\_ST)}$ $t_{h(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	22	
$t_{v(SD\_MT)}$		Master transmitter (after enable edge)	-	20	
$t_{h(SD\_MT)}$	Data output hold time	Master transmitter (after enable edge)	8	-	

1. Guaranteed by characterization results.
2. 256xFs maximum corresponds to 45 MHz (APB2 xaximum frequency)

Table 97. Synchronous non-multiplexed PSRAM write timings[(1)(2)] (continued)

Symbol	Parameter	Min	Max	Unit
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	0	-	ns
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	0	ns
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	T_{HCLK}−0.5	-	ns
$t_{d(CLKL-Data)}$	FMC_D[15:0] valid data after FMC_CLK low	-	2.5	ns
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	0	-	ns
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	T_{HCLK}−0.5	-	ns
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	4		
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	0		

1. C_L = 30 pF.
2. Guaranteed by characterization results.

PC Card/CompactFlash controller waveforms and timings

Figure 63 through *Figure 68* represent synchronous waveforms, and *Table 98* and *Table 99* provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x04;
- COM.FMC_WaitSetupTime = 0x07;
- COM.FMC_HoldSetupTime = 0x04;
- COM.FMC_HiZSetupTime = 0x00;
- ATT.FMC_SetupTime = 0x04;
- ATT.FMC_WaitSetupTime = 0x07;
- ATT.FMC_HoldSetupTime = 0x04;
- ATT.FMC_HiZSetupTime = 0x00;
- IO.FMC_SetupTime = 0x04;
- IO.FMC_WaitSetupTime = 0x07;
- IO.FMC_HoldSetupTime = 0x04;
- IO.FMC_HiZSetupTime = 0x00;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 68. PC Card/CompactFlash controller waveforms for I/O space write access

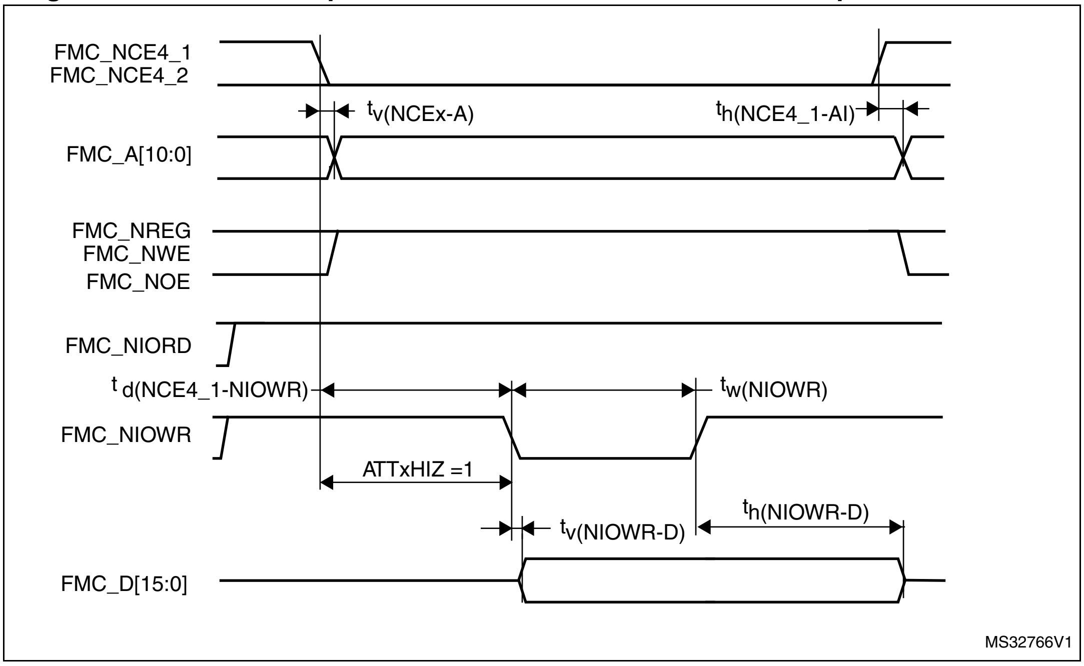


Table 98. Switching characteristics for PC Card/CF read and write cycles in attribute/common space(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{v(NCEx-A)}$	FMC_Ncex low to FMC_Ay valid	-	0	ns
$t_{h(NCEx\_AI)}$	FMC_NCEx high to FMC_Ax invalid	0	-	ns
$t_{d(NREG-NCEx)}$	FMC_NCEx low to FMC_NREG valid	-	1	ns
$t_{h(NCEx-NREG)}$	FMC_NCEx high to FMC_NREG invalid	$T_{HCLK} - 2$	-	ns
$t_{d(NCEx-NWE)}$	FMC_NCEx low to FMC_NWE low	-	$5T_{HCLK}$	ns
$t_{w(NWE)}$	FMC_NWE low width	$8T_{HCLK} - 0.5$	$8T_{HCLK}+0.5$	ns
$t_{d(NWE\_NCEx)}$	FMC_NWE high to FMC_NCEx high	$5T_{HCLK}+1$	-	ns
$t_{V(NWE-D)}$	FMC_NWE low to FMC_D[15:0] valid	-	0	ns
$t_{h(NWE-D)}$	FMC_NWE high to FMC_D[15:0] invalid	$9T_{HCLK} - 0.5$	-	ns
$t_{d(D-NWE)}$	FMC_D[15:0] valid before FMC_NWE high	$13T_{HCLK} - 3$		ns
$t_{d(NCEx-NOE)}$	FMC_NCEx low to FMC_NOE low	-	$5T_{HCLK}$	ns
$t_{w(NOE)}$	FMC_NOE low width	$8\ T_{HCLK} - 0.5$	$8\ T_{HCLK}+0.5$	ns
$t_{d(NOE\_NCEx)}$	FMC_NOE high to FMC_NCEx high	$5T_{HCLK} - 1$	-	ns
$t_{su\ (D-NOE)}$	FMC_D[15:0] valid data before FMC_NOE high	T_{HCLK}	-	ns
$t_{h(NOE-D)}$	FMC_NOE high to FMC_D[15:0] invalid	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 99. Switching characteristics for PC Card/CF read and write cycles in I/O space(1)(2)

Symbol	Parameter	Min	Max	Unit
tw(NIOWR)	FMC_NIOWR low width	$8T_{HCLK} - 0.5$	-	ns
tv(NIOWR-D)	FMC_NIOWR low to FMC_D[15:0] valid	-	0	ns
th(NIOWR-D)	FMC_NIOWR high to FMC_D[15:0] invalid	$9T_{HCLK} - 2$	-	ns
td(NCE4_1-NIOWR)	FMC_NCE4_1 low to FMC_NIOWR valid	-	$5T_{HCLK}$	ns
th(NCEx-NIOWR)	FMC_NCEx high to FMC_NIOWR invalid	$5T_{HCLK}$	-	ns
td(NIORD-NCEx)	FMC_NCEx low to FMC_NIORD valid	-	$5T_{HCLK}$	ns
th(NCEx-NIORD)	FMC_NCEx high to FMC_NIORD) valid	$6T_{HCLK}+2$	-	ns
tw(NIORD)	FMC_NIORD low width	$8T_{HCLK} - 0.5$	$8T_{HCLK}+0.5$	ns
tsu(D-NIORD)	FMC_D[15:0] valid before FMC_NIORD high	T_{HCLK}	-	ns
td(NIORD-D)	FMC_D[15:0] valid after FMC_NIORD high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

NAND controller waveforms and timings

Figure 69 through *Figure 72* represent synchronous waveforms, and *Table 100* and *Table 101* provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x01;
- COM.FMC_WaitSetupTime = 0x03;
- COM.FMC_HoldSetupTime = 0x02;
- COM.FMC_HiZSetupTime = 0x01;
- ATT.FMC_SetupTime = 0x01;
- ATT.FMC_WaitSetupTime = 0x03;
- ATT.FMC_HoldSetupTime = 0x02;
- ATT.FMC_HiZSetupTime = 0x01;
- Bank = FMC_Bank_NAND;
- MemoryDataWidth = FMC_MemoryDataWidth_16b;
- ECC = FMC_ECC_Enable;
- ECCPageSize = FMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

Table 104. SDRAM write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK} - 0.5$	$2T_{HCLK}+0.5$	ns
$t_{d(SDCLKL\_Data)}$	Data output valid time	-	3.5	
$t_{h(SDCLKL\_Data)}$	Data output hold time	0	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	1.5	
$t_{d(SDCLKL\_SDNWE)}$	SDNWE valid time	-	1	
$t_{h(SDCLKL\_SDNWE)}$	SDNWE hold time	0	-	
$t_{d(SDCLKL\_SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL-\_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL\_SDNRAS)}$	SDNRAS valid time	-	2	
$t_{h(SDCLKL\_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS hold time	0	-	
$t_{d(SDCLKL\_NBL)}$	NBL valid time	-	0.5	
$t_{h(SDCLKL\_NBL)}$	NBLoutput time	0	-	

1. CL = 30 pF on data and address lines. CL=15pF on FMC_SDCLK.
2. Guaranteed by characterization results.

Table 105. LPSDR SDRAM write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK} - 0.5$	$2T_{HCLK}+0.5$	ns
$t_{d(SDCLKL\_Data)}$	Data output valid time	-	5	
$t_{h(SDCLKL\_Data)}$	Data output hold time	2	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	2.8	
$t_{d(SDCLKL-SDNWE)}$	SDNWE valid time	-	2	
$t_{h(SDCLKL-SDNWE)}$	SDNWE hold time	1	-	
$t_{d(SDCLKL-SDNE)}$	Chip select valid time	-	1.5	
$t_{h(SDCLKL-SDNE)}$	Chip select hold time	1	-	
$t_{d(SDCLKL-SDNRAS)}$	SDNRAS valid time	-	1.5	
$t_{h(SDCLKL-SDNRAS)}$	SDNRAS hold time	1.5	-	
$t_{d(SDCLKL-SDNCAS)}$	SDNCAS valid time	-	1.5	
$t_{d(SDCLKL-SDNCAS)}$	SDNCAS hold time	1.5	-	
$t_{d(SDCLKL\_NBL)}$	NBL valid time	-	1.5	
$t_{h(SDCLKL-NBL)}$	NBL output time	1.5	-	

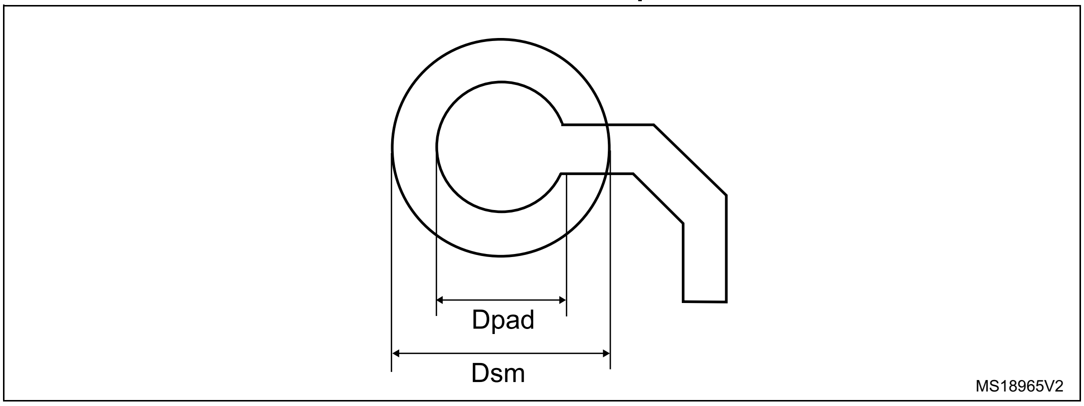
1. CL = 10 pF.
2. Guaranteed by characterization results.

Table 111. WLCSP143 - 143-ball, 4.521x 5.547 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	0.155	0.175	0.195	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3[2]	-	0.025	-	-	0.0010	-
b[3]	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	4.486	4.521	4.556	0.1766	0.1780	0.1794
E	5.512	5.547	5.582	0.2170	0.2184	0.2198
e	-	0.400	-	-	0.0157	-
e1	-	4.000	-	-	0.1575	-
e2	-	4.800	-	-	0.1890	-
F	-	0.2605	-	-	0.0103	-
G	-	0.3735	-	-	0.0147	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

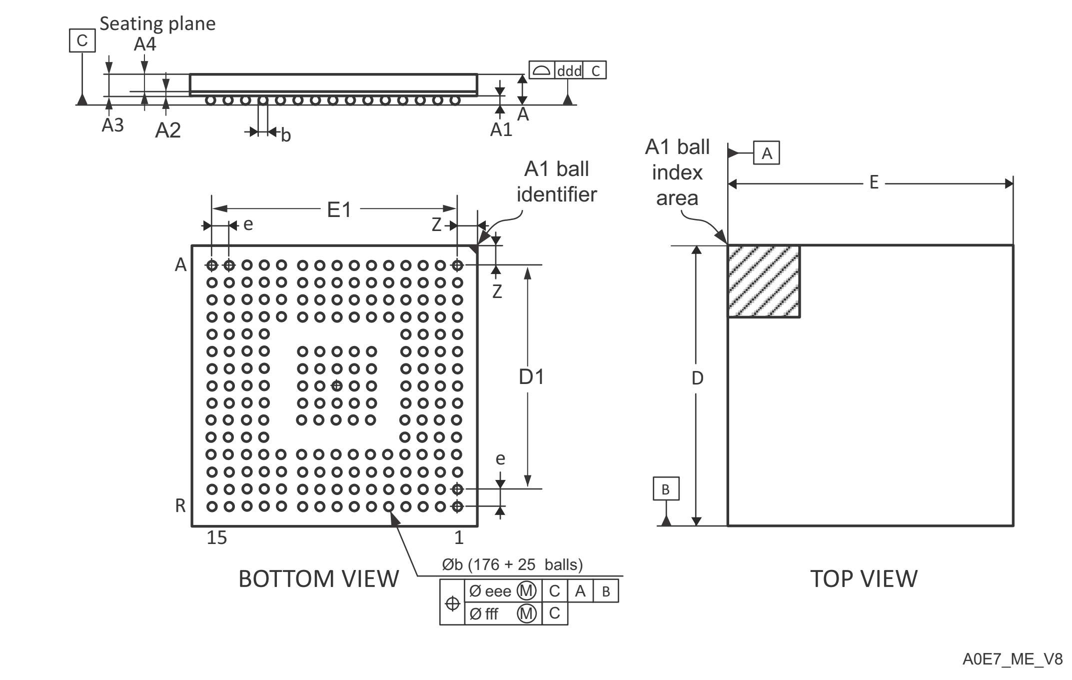
1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 84. WLCSP143 - 143-ball, 4.521x 5.547 mm, 0.4 mm pitch wafer level chip scale recommended footprint



7.7 UFBGA176+25 package information

Figure 98. UFBGA176+25 - ball 10 x 10 mm, 0.65 mm pitch ultra thin fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 118. UFBGA176+25 - ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters			inches(1)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.130	-	-	0.0051	-
A3	-	0.450	-	-	0.0177	-
A4	-	0.320	-	-	0.0126	-
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	9.850	10.000	10.150	0.3878	0.3937	0.3996
D1	-	9.100	-	-	0.3583	-
E	9.850	10.000	10.150	0.3878	0.3937	0.3996
E1	-	9.100	-	-	0.3583	-
e	-	0.650	-	-	0.0256	-
Z	-	0.450	-	-	0.0177	-
ddd	-	-	0.080	-	-	0.0031

8 Part numbering

Table 122. Ordering information scheme

Example: STM32 F 429 V I T 6 xxx

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

F = general-purpose

Device subfamily

427= STM32F427xx, USB OTG FS/HS, camera interface, Ethernet

429= STM32F429xx, USB OTG FS/HS, camera interface, Ethernet, LCD-TFT

Pin count

V = 100 pins

Z = 143 and 144 pins

A = 169 pins

I = 176 pins

B = 208 pins

N = 216 pins

Flash memory size

E = 512 Kbytes of Flash memory

G = 1024 Kbytes of Flash memory

I = 2048 Kbytes of Flash memory

Package

T = LQFP

H = BGA

Y = WLCSP

Temperature range

6 = Industrial temperature range, –40 to 85 °C.

7 = Industrial temperature range, –40 to 105 °C.

Options

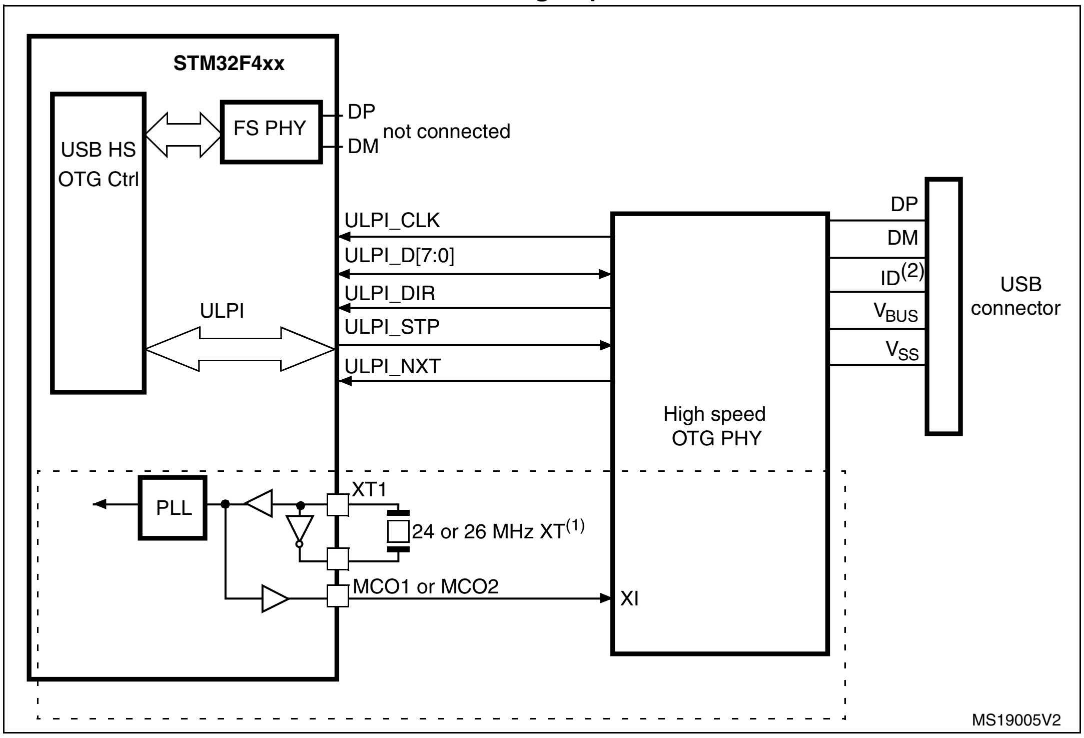
xxx = programmed parts

TR = tape and reel

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

B.2 USB OTG high speed (HS) interface solutions

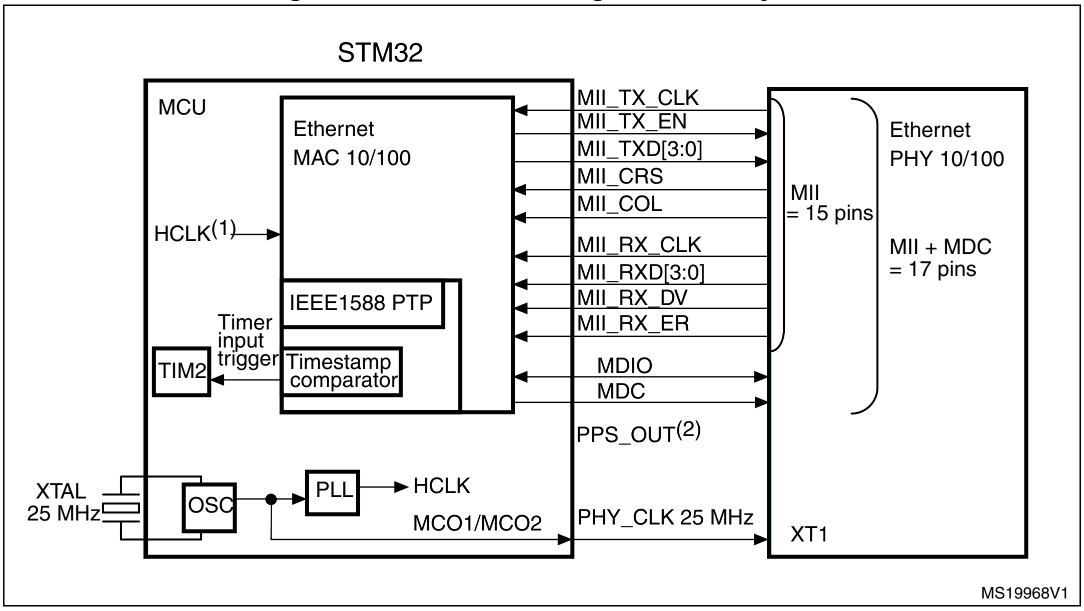
Figure 106. USB controller configured as peripheral, host, or dual-mode and used in high speed mode



1. It is possible to use MCO1 or MCO2 to save a crystal. It is however not mandatory to clock the STM32F42x with a 24 or 26 MHz crystal when using USB HS. The above figure only shows an example of a possible connection.
2. The ID pin is required in dual role only.

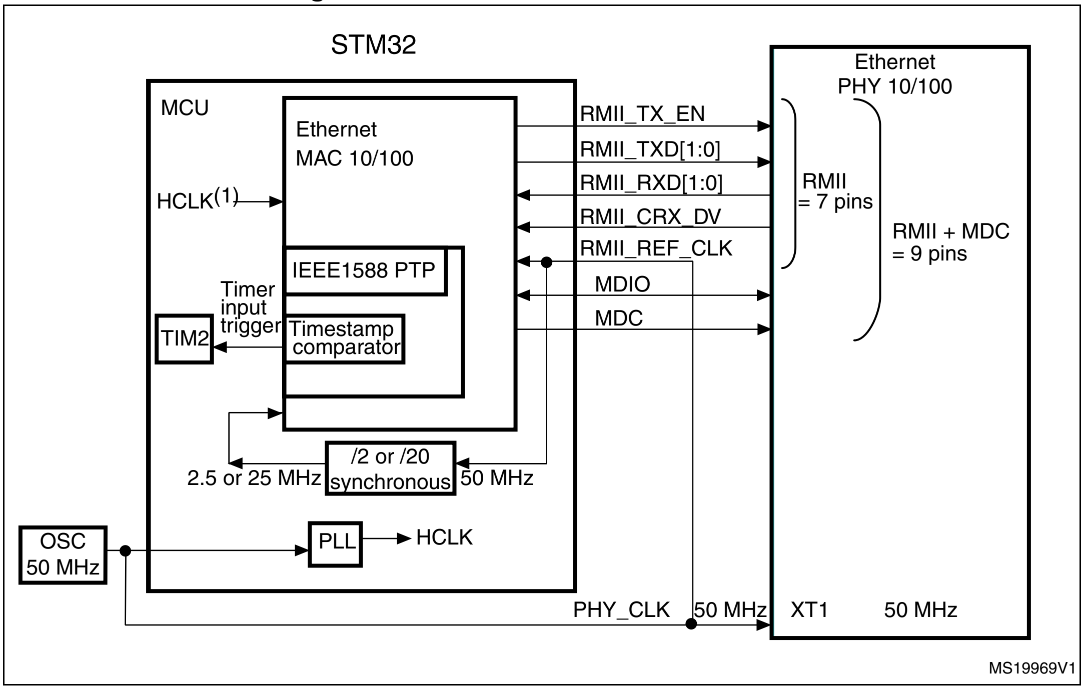
B.3 Ethernet interface solutions

Figure 107. MII mode using a 25 MHz crystal



1. f_{HCLK} must be greater than 25 MHz.
2. Pulse per second when using IEEE1588 PTP optional signal.

Figure 108. RMII with a 50 MHz oscillator



1. f_{HCLK} must be greater than 25 MHz.